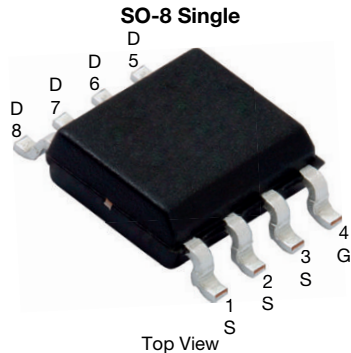




Automotive P-Channel 30 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY

V_{DS} (V)	-30
$R_{DS(on)}$ (Ω) at $V_{GS} = -10$ V	0.0085
$R_{DS(on)}$ (Ω) at $V_{GS} = -4.5$ V	0.0200
I_D (A)	-22
Configuration	Single

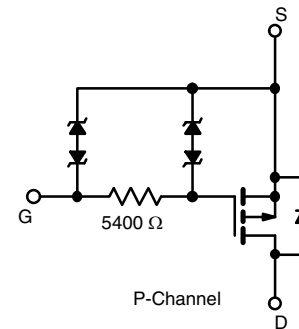


FEATURES

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- ESD Protection: 3000 V
- 100 % UIS tested
- Material categorization:
for definitions of compliance please see
www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE



ORDERING INFORMATION

Package	SO-8
Lead (Pb)-free and Halogen-free	SQ4483BEEY-T1-GE3

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current	I_D	$T_C = 25$ °C	-22
		$T_C = 125$ °C	-13
Continuous Source Current (Diode Conduction)	I_S	-6	A
Pulsed Drain Current ^a	I_{DM}	-84	
Single Pulse Avalanche Current	I_{AS}	-7	
Single Pulse Avalanche Energy	E_{AS}	245	mJ
Maximum Power Dissipation ^a	P_D	$T_C = 25$ °C	7
		$T_C = 125$ °C	2
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +175	°C

THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-Ambient	R_{thJA}	85	°C/W
Junction-to-Foot (Drain)	R_{thJF}	21	

Notes

- a. Pulse test; pulse width ≤ 300 μ s, duty cycle ≤ 2 %.
b. When mounted on 1" square PCB (FR4 material).

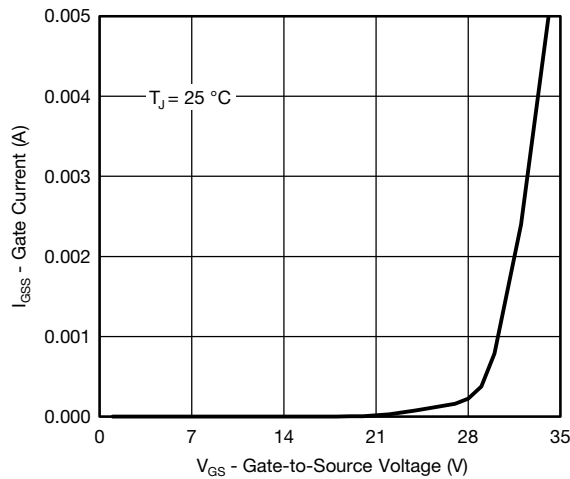
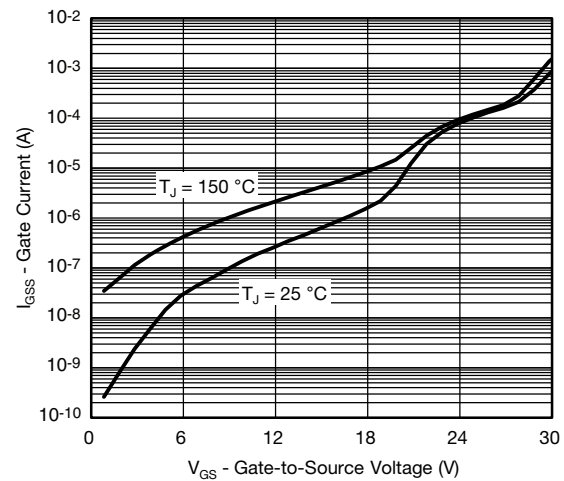
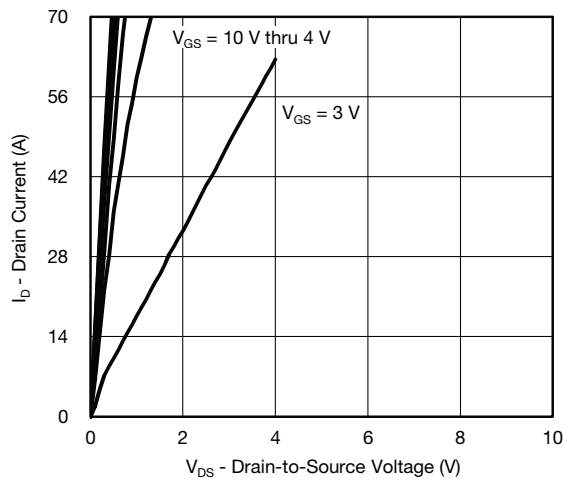
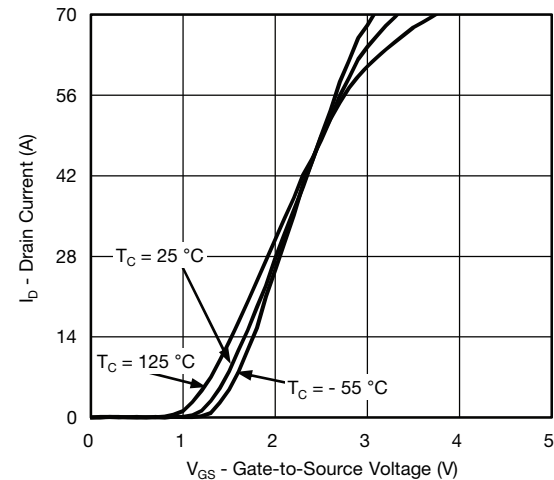
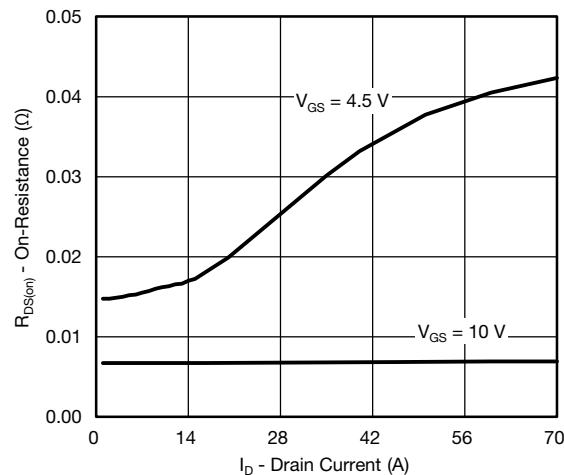
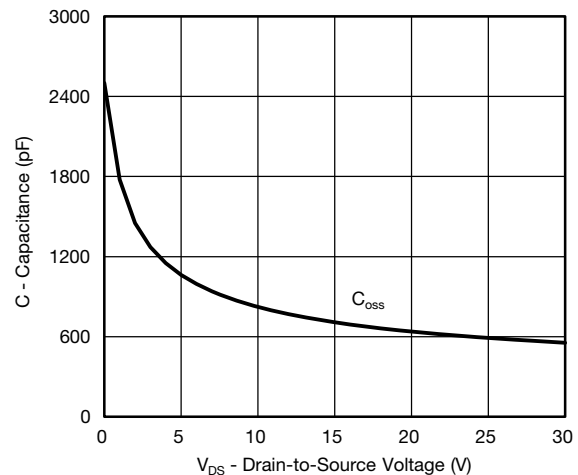


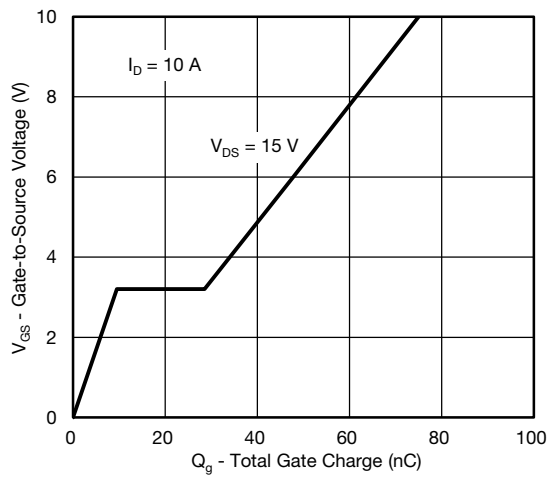
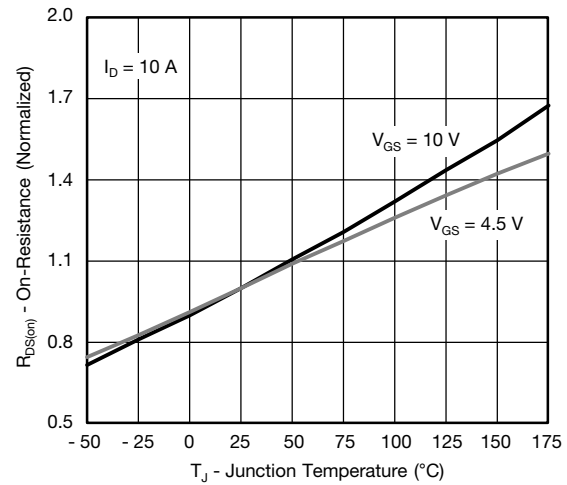
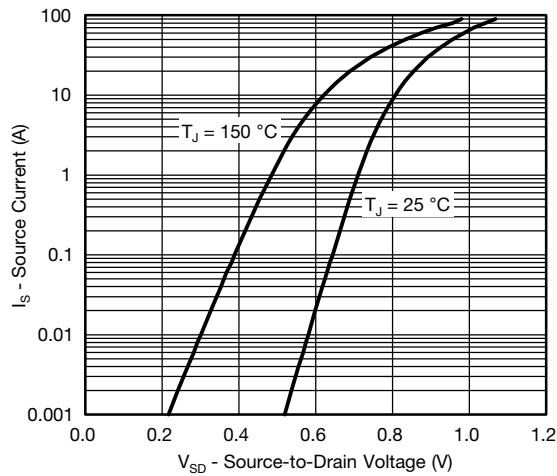
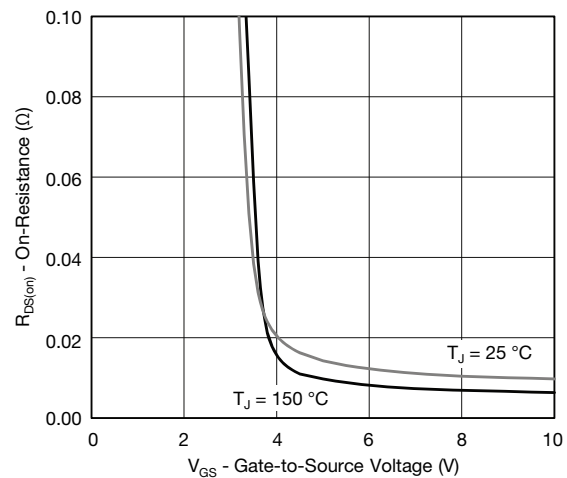
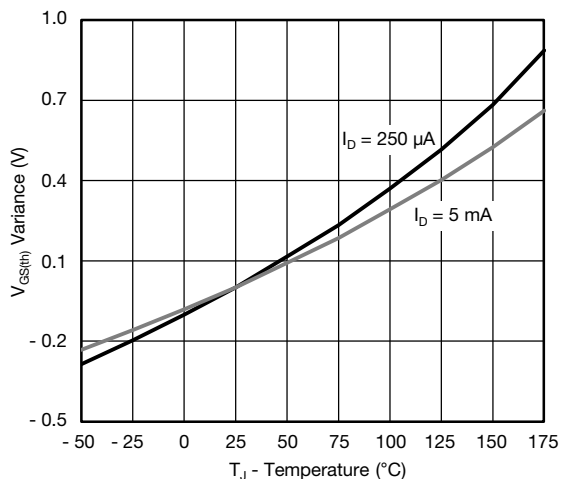
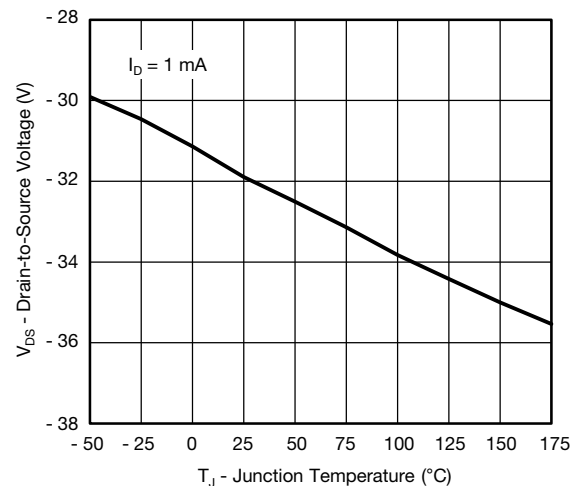
SPECIFICATIONS (T _C = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = -250 μA		-30	-	-	V
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250 μA		-1.5	-2.0	-2.5	
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V		-	-	± 1	mA
		V _{DS} = 0 V, V _{GS} = ± 12 V		-	-	± 2	
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = -30 V	-	-	-1	μA
		V _{GS} = 0 V	V _{DS} = -30 V, T _J = 125 °C	-	-	-50	
		V _{GS} = 0 V	V _{DS} = -30 V, T _J = 175 °C	-	-	-150	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = -10 V	V _{DS} ≤ -5 V	-30	-	-	A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = -10 V	I _D = -10 A	-	0.0070	0.0085	Ω
		V _{GS} = -10 V	I _D = -10 A, T _J = 125 °C	-	-	0.0130	
		V _{GS} = -10 V	I _D = -10 A, T _J = 175 °C	-	-	0.0150	
		V _{GS} = -4.5 V	I _D = -7 A	-	0.0160	0.0200	
Forward Transconductance ^b	g _{fs}	V _{DS} = -10 V, I _D = -10 A		-	32	-	S
Dynamic ^b							
Output Capacitance	C _{oss}	V _{GS} = 0 V	V _{DS} = -15 V, f = 1 MHz	-	712	890	pF
Total Gate Charge ^c	Q _g	V _{GS} = -10 V	V _{DS} = -15 V, I _D = -10 A	-	75	113	nC
Gate-Source Charge ^c	Q _{gs}			-	9.5	-	
Gate-Drain Charge ^c	Q _{gd}			-	19	-	
Turn-On Delay Time ^c	t _{d(on)}	V _{DD} = -15 V, R _L = 1.5 Ω I _D ≅ -10 A, V _{GEN} = -10 V, R _g = 1 Ω		-	38	57	μs
Rise Time ^c	t _r			-	82	123	
Turn-Off Delay Time ^c	t _{d(off)}			-	134	201	
Fall Time ^c	t _f			-	178	214	
Source-Drain Diode Ratings and Characteristics ^b							
Pulsed Current ^a	I _{SM}			-	-	-84	A
Forward Voltage	V _{SD}	I _F = -3 A, V _{GS} = 0 V		-	-0.75	-1.2	V

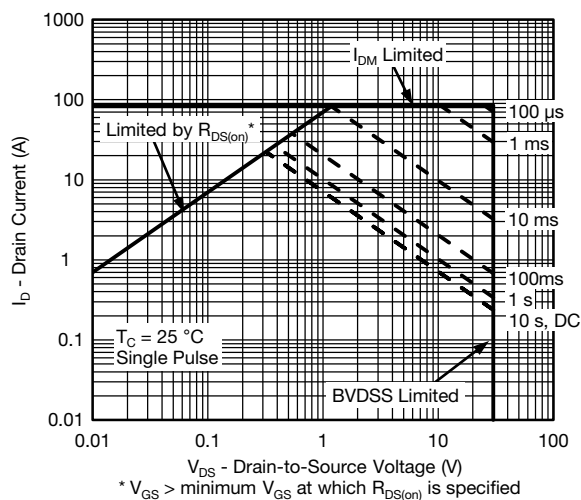
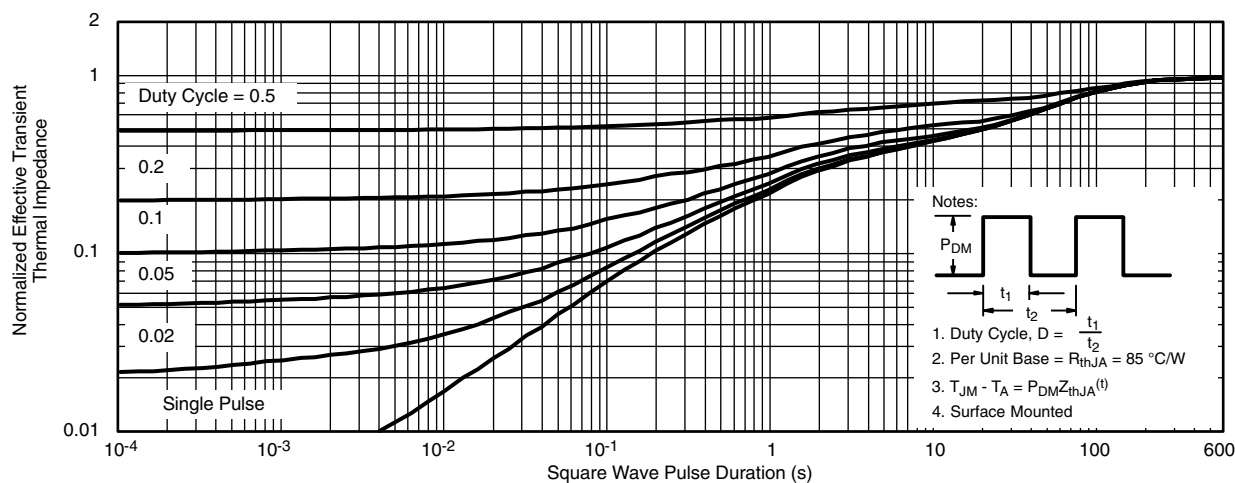
Notes

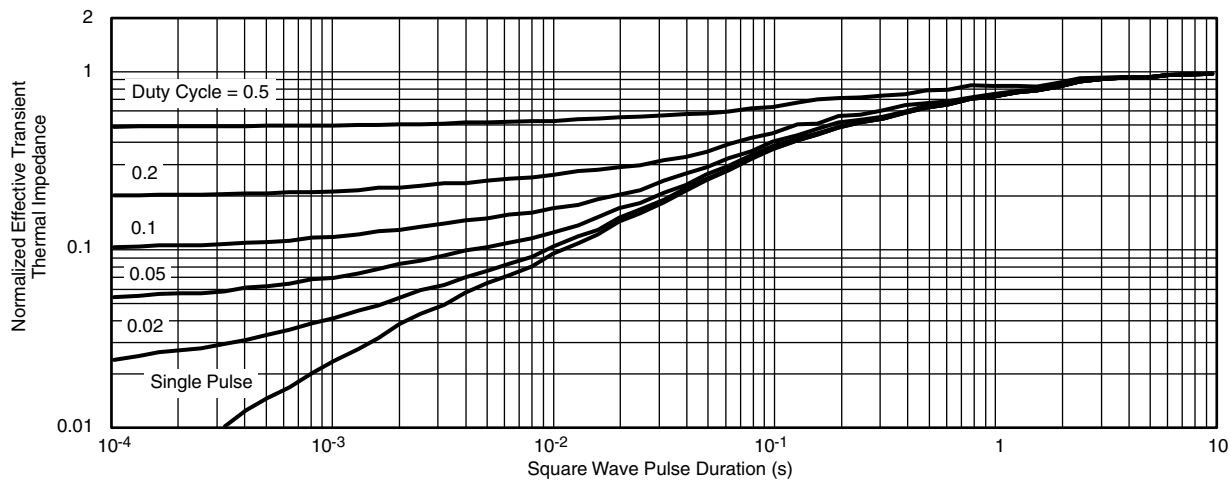
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)**Gate Current vs. Gate-Source Voltage****Gate Current vs. Gate-Source Voltage****Output Characteristics****Transfer Characteristics****On-Resistance vs. Drain Current****Capacitance**

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)**Gate Charge****On-Resistance vs. Junction Temperature****Source Drain Diode Forward Voltage****On-Resistance vs. Gate-to-Source Voltage****Threshold Voltage****Drain Source Breakdown vs. Junction Temperature**


THERMAL RATINGS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

Safe Operating Area

Normalized Thermal Transient Impedance, Junction-to-Ambient


THERMAL RATINGS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)


Normalized Thermal Transient Impedance, Junction-to-Foot

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient ($25\text{ }^{\circ}\text{C}$)
 - Normalized Transient Thermal Impedance Junction-to-Foot ($25\text{ }^{\circ}\text{C}$)
- are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?67097.

SOIC (NARROW): 8-LEAD

JEDEC Part Number: MS-012



DIM	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	1.35	1.75	0.053	0.069
A ₁	0.10	0.20	0.004	0.008
B	0.35	0.51	0.014	0.020
C	0.19	0.25	0.0075	0.010
D	4.80	5.00	0.189	0.196
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.020
L	0.50	0.93	0.020	0.037
q	0°	8°	0°	8°
S	0.44	0.64	0.018	0.026
ECN: C-06527-Rev. I, 11-Sep-06				
DWG: 5498				

RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads
Dimensions in Inches/(mm)

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